10-PY07ANA100RG01-LH23L68Y

datasheet

***flow*ANPFC 1** **650 V / 100 A**

Topology features

- Advanced Neutral Boost PFC
- Integrated DC capacitor
- Kelvin Emitter for improved switching performance
- Temperature sensor

Component features

- High efficiency in hard switching and resonant topologies
- High speed switching
- Low gate charge

Housing features

- Base isolation: Al_2O_3
- Convex shaped substrate for superior thermal contact
- Thermo-mechanical push-and-pull force relief
- Press-fit pin
- Reliable cold welding connection

Extra features

- SiC Boost Diode

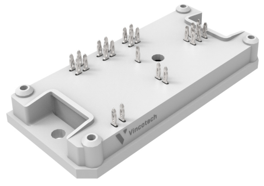
Target applications

- Charging Stations

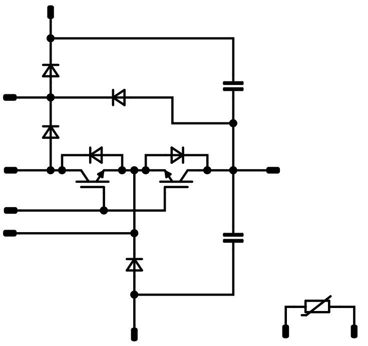
Types

- 10-PY07ANA100RG01-LH23L68Y

flow 1 12 mm housing



Schematic



Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions		Value	Unit
Negative Neutral Point Switch					
Collector-emitter voltage	V_{CES}			650	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$	T_s = 80 °C	81	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}		400	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	132	W
Gate-emitter voltage	V_{GES}			±30	V
Maximum junction temperature	T_{jmax}			175	°C
Positive Neutral Point Switch					
Collector-emitter voltage	V_{CES}			650	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$	T_s = 80 °C	81	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}		400	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	132	W
Gate-emitter voltage	V_{GES}			±30	V
Maximum junction temperature	T_{jmax}			175	°C
Negative Boost Diode					
Peak repetitive reverse voltage	V_{RRM}			650	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	36	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		120	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 8,3 ms	T_j = 25 °C	120	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	64	W
Maximum junction temperature	T_{jmax}			175	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions		Value	Unit
Positive Boost Diode					
Peak repetitive reverse voltage	V_{RRM}			650	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	36	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		120	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 8,3 ms	T_j = 25 °C	120	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	64	W
Maximum junction temperature	T_{jmax}			175	°C
Negative Neutral Point Diode					
Peak repetitive reverse voltage	V_{RRM}			1600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	86	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 10 ms	T_j = 150 °C	890	A
Surge current capability	I^2t			3960	A^2s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	91	W
Maximum junction temperature	T_{jmax}			150	°C
Positive Neutral Point Diode					
Peak repetitive reverse voltage	V_{RRM}			1600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	118	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 10 ms	T_j = 150 °C	1380	A
Surge current capability	I^2t			9520	A^2s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	122	W
Maximum junction temperature	T_{jmax}			150	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions		Value	Unit
Positive Boost Diode Protection Diode					
Peak repetitive reverse voltage	V_{RRM}			650	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	23	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		40	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	39	W
Maximum junction temperature	T_{jmax}			175	°C
Positive Boost Blocking Diode					
Peak repetitive reverse voltage	V_{RRM}			1600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	86	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 10 ms	T_j = 150 °C	890	A
Surge current capability	I^2t			3960	A^2s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	91	W
Maximum junction temperature	T_{jmax}			150	°C
Capacitor (DC)					
Maximum DC voltage	V_{MAX}			630	V
Operation Temperature	T_{op}			-55 ... 125	°C
Module Properties					
Thermal Properties					
Storage temperature	T_{stg}			-40…+125	°C
Operation temperature under switching condition	T_{jop}			-40…+(T_{jmax} - 25)	°C
Isolation Properties					
Isolation voltage	V_{isol}	DC Test Voltage*	t_p = 2 s	6000	V
Isolation voltage	V_{isol}	AC Voltage	t_p = 1 min	2500	V
Creepage distance				>12,7	mm
Clearance				7.55	mm
Comparative Tracking Index	CTI			≥ 200	

*100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	Unit
Negative Neutral Point Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$			5	0,066	25	5	6	7	V
Collector-emitter saturation voltage	V_{CEsat}		15		100	25 125 150		1,5 1,66 1,7	1,9(1)	V
Collector-emitter cut-off current	I_{CES}		0	650		25			0,02	mA
Gate-emitter leakage current	I_{GES}		30	0		25			0,4	µA
Internal gate resistance	r_g							None		Ω
Input capacitance	C_{ies}	f = 1 Mhz	0	30		25		8400		pF
Output capacitance	C_{oes}	f = 1 Mhz	0	30		25		208		pF
Reverse transfer capacitance	C_{res}	f = 1 Mhz	0	30		25		158		pF
Gate charge	Q_g		15	400	100	25		282		nC
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,72		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 4 Ω R_{goff} = 4 Ω	0/15	400	65	25 125 150		68,47 59,23 56,87		ns
Rise time	t_r	R_{gon} = 4 Ω R_{goff} = 4 Ω	0/15	400	65	25 125 150		36,61 36,46 36,3		ns
Turn-off delay time	$t_{d(off)}$	R_{gon} = 4 Ω R_{goff} = 4 Ω	0/15	400	65	25 125 150		198,58 229,53 238,96		ns
Fall time	t_f	R_{gon} = 4 Ω R_{goff} = 4 Ω	0/15	400	65	25 125 150		28,01 44,72 48,75		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=0,053 µC Q_{rFWD}=0,052 µC Q_{rFWD}=0,05 µC	0/15	400	65	25 125 150		0,88 0,926 0,937		mWs
Turn-off energy (per pulse)	E_{off}		0/15	400	65	25 125 150		1,29 1,72 1,85		mWs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Positive Neutral Point Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$			5	0,066	25	5	6	7	V
Collector-emitter saturation voltage	V_{CEsat}		15		100	25 125 150		1,5 1,66 1,7	1,9(1)	V
Collector-emitter cut-off current	I_{CES}		0	650		25			0,02	mA
Gate-emitter leakage current	I_{GES}		30	0		25			0,4	μA
Internal gate resistance	r_g							None		Ω
Input capacitance	C_{ies}	f = 1 Mhz	0	30		25		8400		pF
Output capacitance	C_{oes}							208		pF
Reverse transfer capacitance	C_{res}							158		pF
Gate charge	Q_g		15	400	100	25		282		nC
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,72		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 4 Ω R_{goff} = 4 Ω	0/15	400	65	25 125 150		70,62 60,61 57,85		ns
Rise time	t_r					25 125 150		63,16 62,45 61,92		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		200,34 231,49 240,73		ns
Fall time	t_f					25 125 150		44,92 55,92 60,45		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=0,086 μC Q_{rFWD}=0,082 μC Q_{rFWD}=0,082 μC				25 125 150		1,11 1,18 1,21		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		1,5 2,01 2,16		mWs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Negative Boost Diode										
Static										
Forward voltage	V_F				30	25 125 150		1,39 1,53 1,62	1,55(1)	V
Reverse leakage current	I_R	V_r = 650 V				25 150		6 90	600	µA
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,48		K/W
Dynamic										
Peak recovery current	I_{RRM}	d*i*/d*t*=2561 A/µs d*i*/d*t*=2654 A/µs d*i*/d*t*=2217 A/µs	0/15	400	65	25 125 150		10,24 9,48 9,23		A
Reverse recovery time	t_{rr}					25 125 150		8,9 9,06 8,97		ns
Recovered charge	Q_r					25 125 150		0,053 0,052 0,05		µC
Reverse recovered energy	E_{rec}					25 125 150		$8,891x10^{-3}$ $8,195x10^{-3}$ $7,967x10^{-3}$		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		3321,92 2781,09 2867,81		A/µs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Positive Boost Diode										
Static										
Forward voltage	V_F				30	25 125 150		1,39 1,53 1,62	1,55(1)	V
Reverse leakage current	I_R	V_r = 650 V				25 150		6 90	600	µA
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,48		K/W
Dynamic										
Peak recovery current	I_{RRM}	d*i*/d*t*=1890 A/µs d*i*/d*t*=1493 A/µs d*i*/d*t*=1275 A/µs	0/15	400	65	25 125 150		5,54 5,34 5,54		A
Reverse recovery time	t_{rr}					25 125 150		26,26 26,67 27,05		ns
Recovered charge	Q_r					25 125 150		0,086 0,082 0,082		µC
Reverse recovered energy	E_{rec}					25 125 150		0,021 0,019 0,019		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		638,68 636,5 666,84		A/µs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Negative Neutral Point Diode										
Static										
Forward voltage	V_F				60	25 125 150		1,06 0,99 0,97	1,5(1)	V
Reverse leakage current	I_R	V_r = 1600 V				25 150			100 2	µA
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,77		K/W
Positive Neutral Point Diode										
Static										
Forward voltage	V_F				110	25 125 150		1,11 1,03 1,03	1,5(1)	V
Reverse leakage current	I_R	V_r = 1600 V				25 150			100 2000	µA
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,57		K/W

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	Unit
Positive Boost Diode Protection Diode										
Static										
Forward voltage	V_F				20	25 125 150	1,23	1,74 1,65 1,61	1,87(1)	V
Reverse leakage current	I_R	V_r = 650 V				25			0,24	µA
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						2,46		K/W
Positive Boost Blocking Diode										
Static										
Forward voltage	V_F				60	25 125 150		1,06 0,99 0,97	1,5(1)	V
Reverse leakage current	I_R	V_r = 1600 V				25 150			100 2	µA
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,77		K/W
Capacitor (DC)										
Static										
Capacitance	C	DC bias voltage = 0 V				25		100		nF
Tolerance							-10		10	%

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Thermistor										
Static										
Rated resistance	R					25		22		kΩ
Deviation of R_{100}	$\Delta_{R/R}$	R_{100} = 1484 Ω				100	-5		5	%
Power dissipation	P					25		130		mW
Power dissipation constant	d					25		1,5		mW/K
B-value	$B_{(25/50)}$	Tol. ±1 %						3962		K
B-value	$B_{(25/100)}$	Tol. ±1 %						4000		K
Vincotech Thermistor Reference									I	

(1) Value at chip level

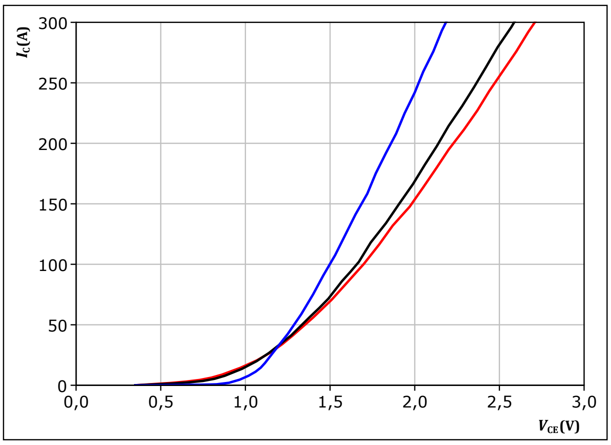
(2) Only valid with pre-applied Vincotech thermal interface material.

Negative Neutral Point Switch Characteristics

figure 1. **IGBT**

Typical output characteristics

I_C = f(V_{CE})

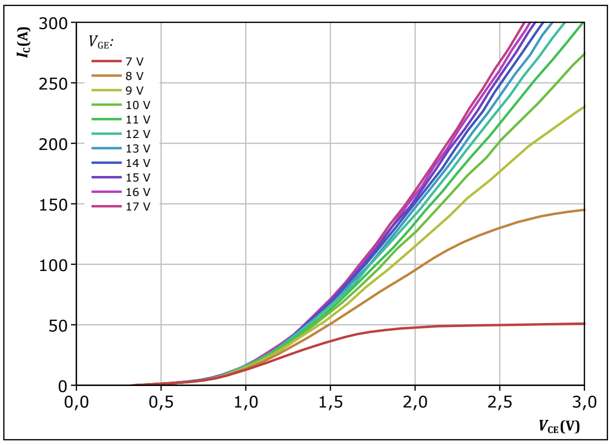


t_p =	250	μs		25 °C
V_{GE} =	15	V	T_j:	125 °C
				150 °C

figure 2. **IGBT**

Typical output characteristics

I_C = f(V_{CE})



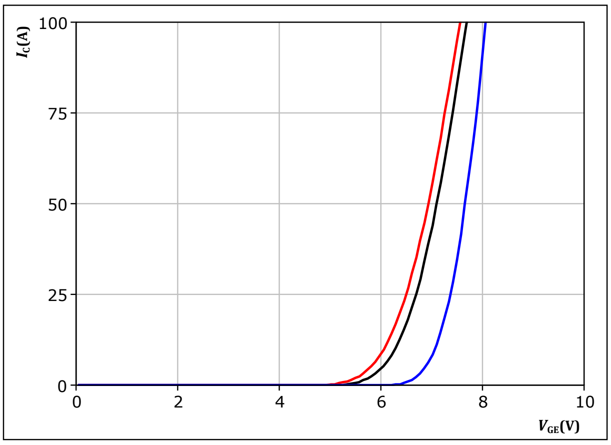
t_p =	250	μs
T_j =	150	°C

V_{GE} from 7 V to 17 V in steps of 1 V

figure 3. **IGBT**

Typical transfer characteristics

I_C = f(V_{GE})

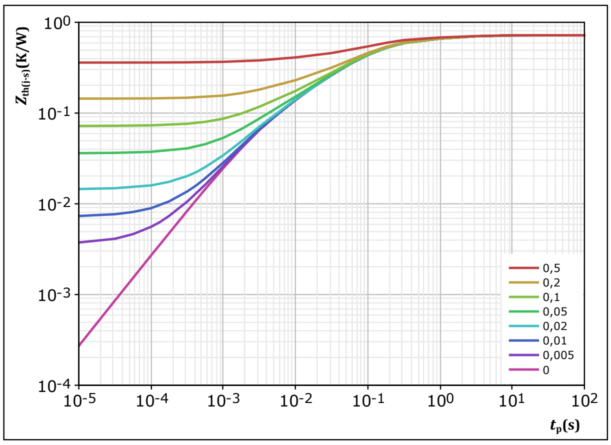


t_p =	250	μs		25 °C
V_{CE} =	10	V	T_j:	125 °C
				150 °C

figure 4. **IGBT**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D =	t_p / T	
$R_{th(j-s)}$ =	0,72	K/W

IGBT thermal model values

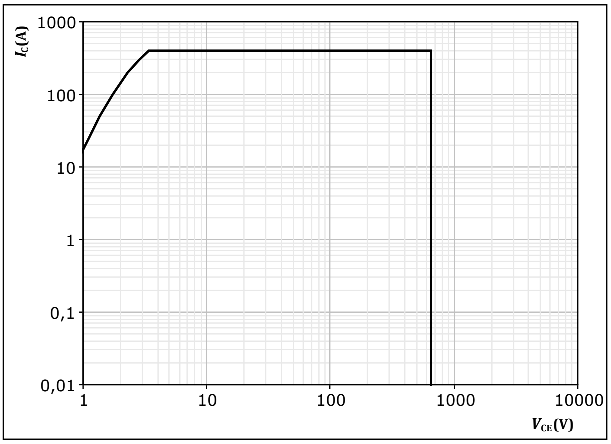
R (K/W)	τ (s)
6,28E-02	2,57E+00
9,58E-02	5,54E-01
3,57E-01	1,08E-01
1,45E-01	2,46E-02
6,02E-02	3,37E-03

Negative Neutral Point Switch Characteristics

figure 5.	IGBT

Safe operating area

I_C = f(V_{CE})



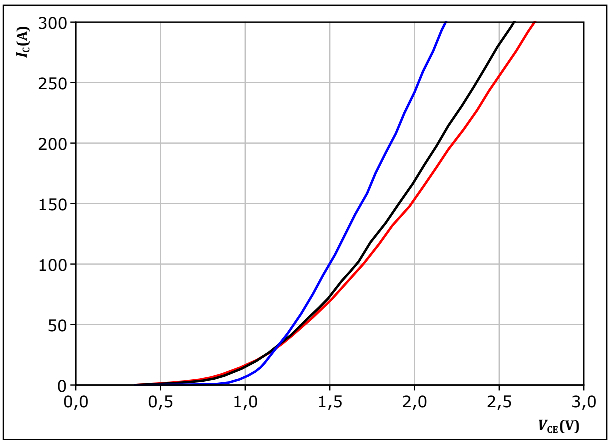
D =	single pulse	
T_s =	80	°C
V_{GE} =	15	V
T_j =	T_{jmax}	

Positive Neutral Point Switch Characteristics

figure 6. **IGBT**

Typical output characteristics

I_C = f(V_{CE})



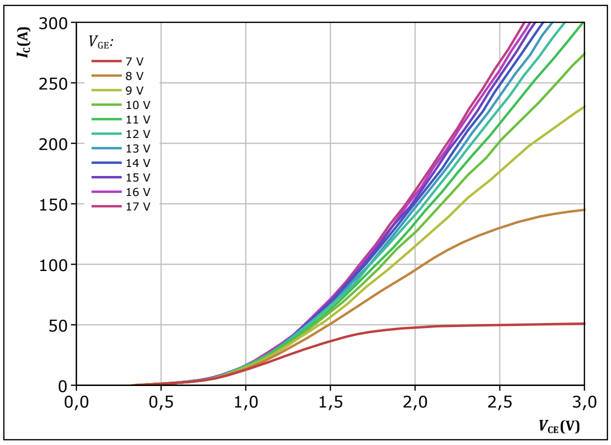
t_p = 250 µs
V_{GE} = 15 V

T_j: 25 °C, 125 °C, 150 °C

figure 7. **IGBT**

Typical output characteristics

I_C = f(V_{CE})

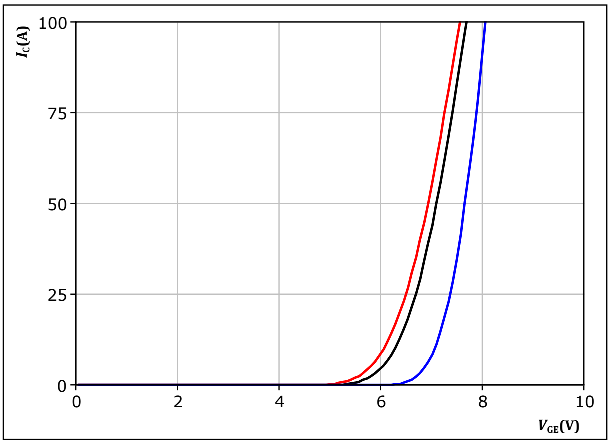


t_p = 250 µs
T_j = 150 °C
V_{GE} from 7 V to 17 V in steps of 1 V

figure 8. **IGBT**

Typical transfer characteristics

I_C = f(V_{GE})



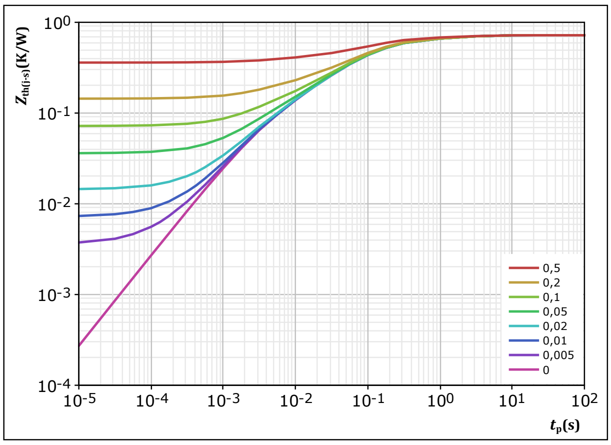
t_p = 250 µs
V_{CE} = 10 V

T_j: 25 °C, 125 °C, 150 °C

figure 9. **IGBT**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T
$R_{th(j-s)}$ = 0,72 K/W

IGBT thermal model values

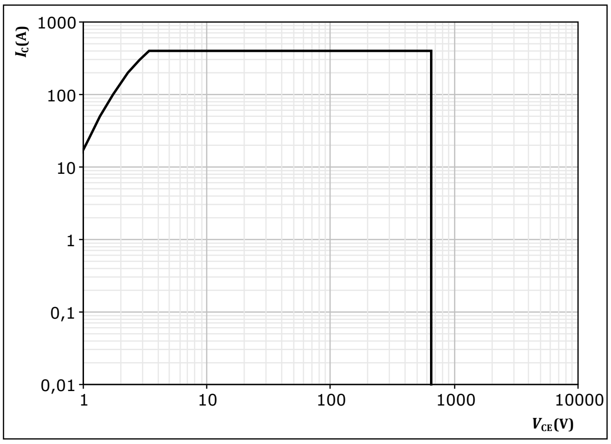
R (K/W)	τ (s)
6,28E-02	2,57E+00
9,58E-02	5,54E-01
3,57E-01	1,08E-01
1,45E-01	2,46E-02
6,02E-02	3,37E-03

Positive Neutral Point Switch Characteristics

figure 10. **IGBT**

Safe operating area

I_C = f(V_{CE})



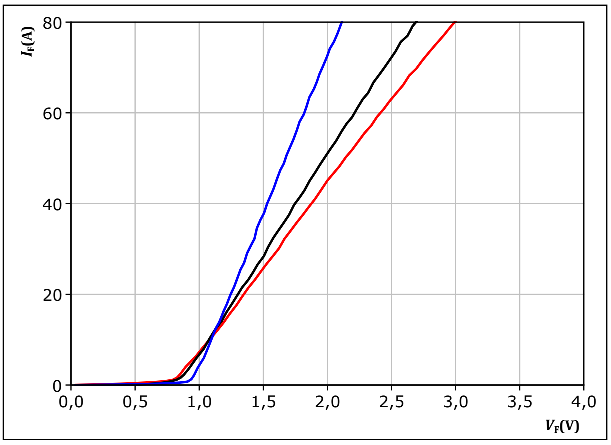
D =	single pulse	
T_s =	80	°C
V_{GE} =	15	V
T_j =	T_{jmax}	

Negative Boost Diode Characteristics

figure 11. FWD

Typical forward characteristics

$I_F = f(V_F)$



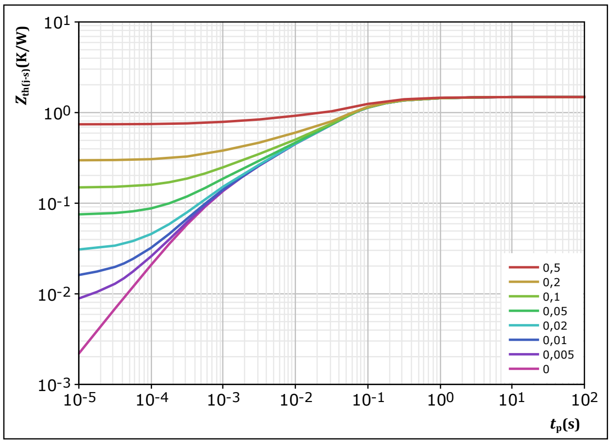
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 12. FWD

Transient thermal impedance as a function of pulse width

$Z_{th(j\text{-}s)} = f(t_p)$



$D = t_p / T$

$R_{th(j\text{-}s)}$ = 1,485 K/W

FWD thermal model values

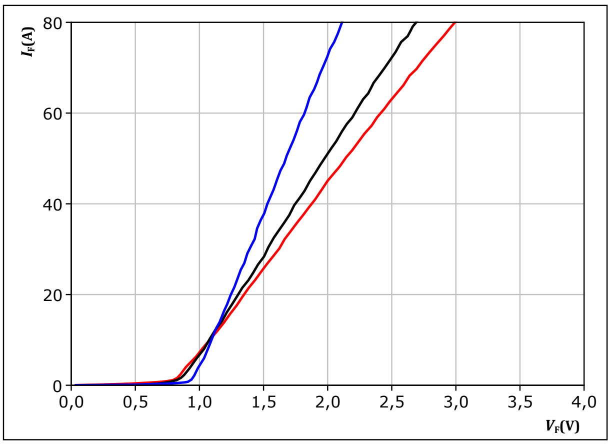
R (K/W)	τ (s)
6,45E-02	1,95E+00
2,63E-01	2,25E-01
8,47E-01	5,10E-02
2,23E-01	4,17E-03
8,76E-02	5,85E-04

Positive Boost Diode Characteristics

figure 13. **FWD**

Typical forward characteristics

$I_F = f(V_F)$



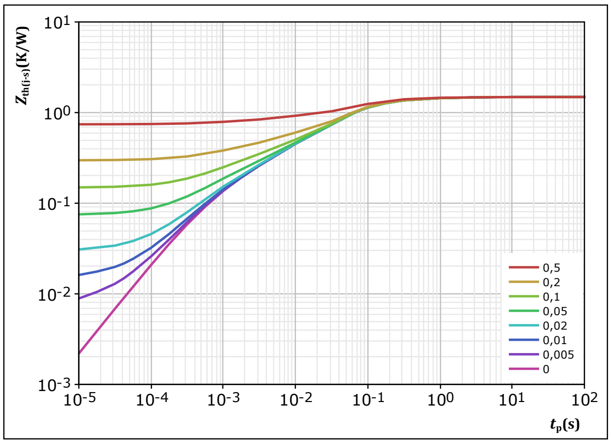
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 14. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



$D = t_p / T$

$R_{th(j-s)}$ = 1,485 K/W

FWD thermal model values

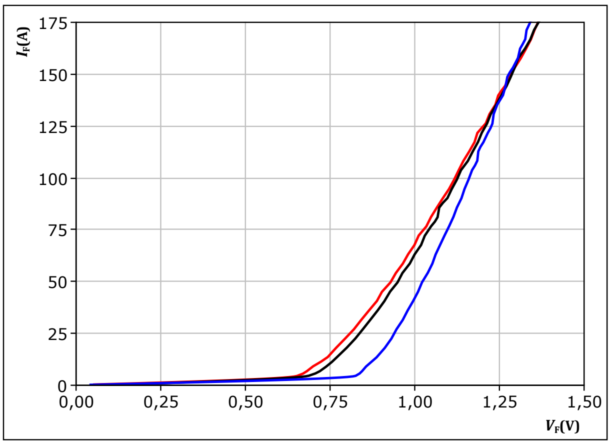
R (K/W)	τ (s)
6,45E-02	1,95E+00
2,63E-01	2,25E-01
8,47E-01	5,10E-02
2,23E-01	4,17E-03
8,76E-02	5,85E-04

Negative Neutral Point Diode Characteristics

figure 15. **Rectifier**

Typical forward characteristics

$I_F = f(V_F)$



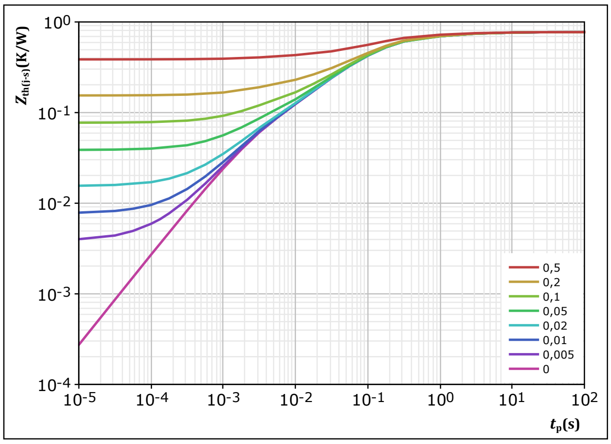
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 16. **Rectifier**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 0,772 K/W

Rectifier thermal model values

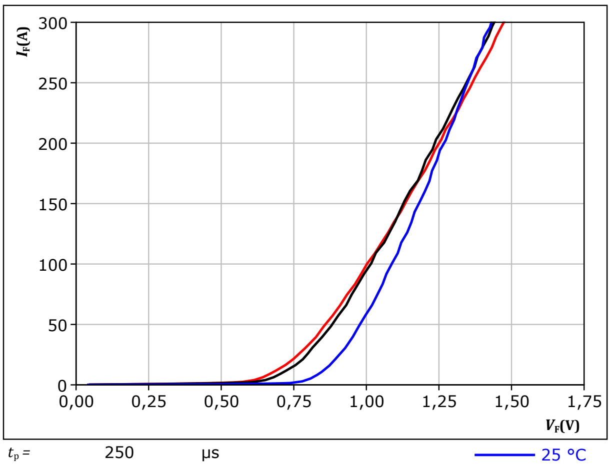
R (K/W)	τ (s)
2,82E-02	8,69E+00
1,16E-01	1,22E+00
4,16E-01	1,44E-01
1,62E-01	2,97E-02
5,02E-02	2,64E-03

Positive Neutral Point Diode Characteristics

figure 17. **Rectifier**

Typical forward characteristics

I_F = f(V_F)



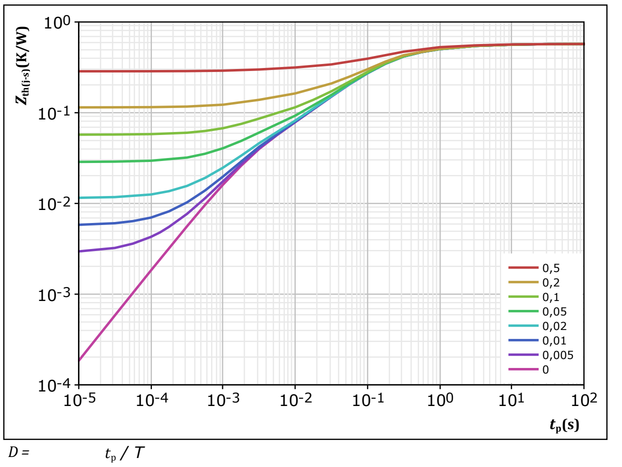
t_p = 250 μs

T_j: 25 °C / 125 °C / 150 °C

figure 18. **Rectifier**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 0,572 K/W

Rectifier thermal model values

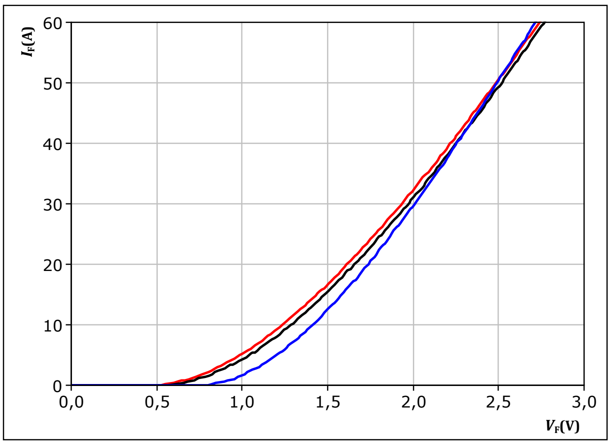
R (K/W)	τ (s)
1,96E-02	1,44E+01
9,85E-02	1,51E+00
3,15E-01	1,85E-01
1,04E-01	3,37E-02
3,57E-02	2,61E-03

Positive Boost Diode Protection Diode Characteristics

figure 19. **FWD**

Typical forward characteristics

I_F = f(V_F)



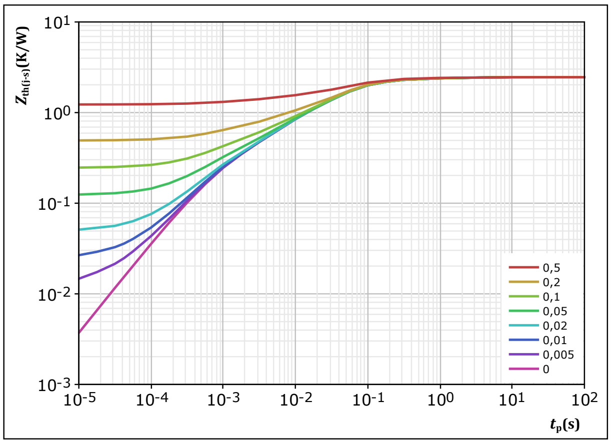
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 20. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 2,457 K/W

FWD thermal model values

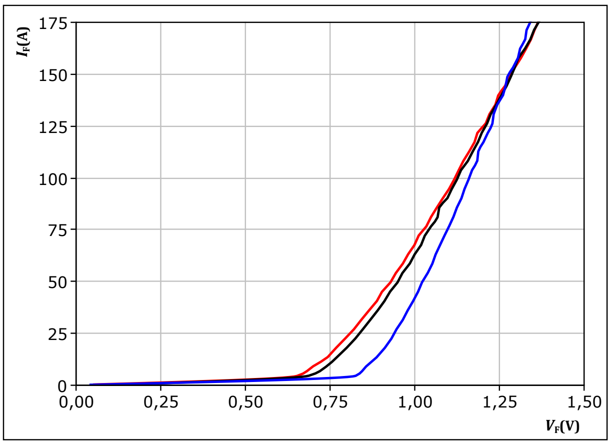
R (K/W)	τ (s)
1,00E-01	2,27E+00
3,37E-01	2,00E-01
1,37E+00	4,58E-02
4,51E-01	6,21E-03
2,01E-01	7,45E-04

Positive Boost Blocking Diode Characteristics

figure 21. **Rectifier**

Typical forward characteristics

I_F = f(V_F)



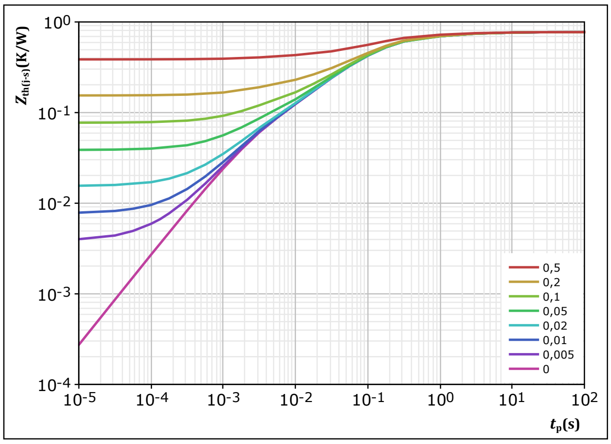
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 22. **Rectifier**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 0,772 K/W

Rectifier thermal model values

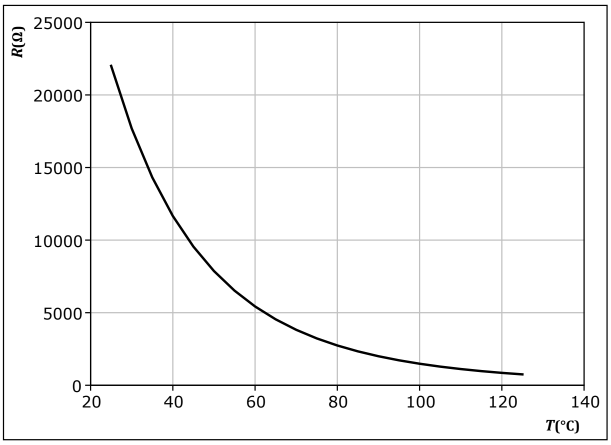
R (K/W)	τ (s)
2,82E-02	8,69E+00
1,16E-01	1,22E+00
4,16E-01	1,44E-01
1,62E-01	2,97E-02
5,02E-02	2,64E-03

Thermistor Characteristics

figure 23. **Thermistor**

Typical NTC characteristic as function of temperature

R_T = f(T)

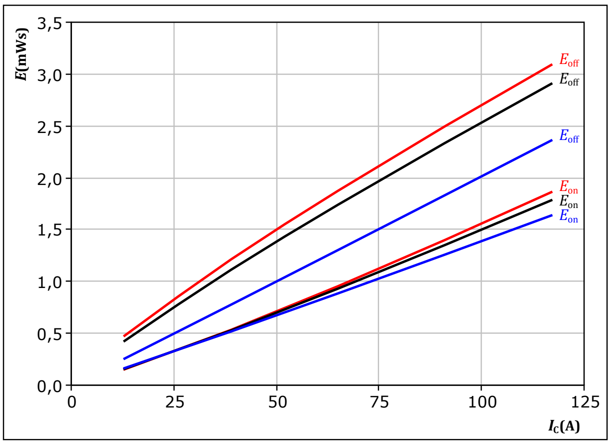


Negative Neutral Point Switching Characteristics

figure 24. **IGBT**

Typical switching energy losses as a function of collector current

$E = f(I_C)$



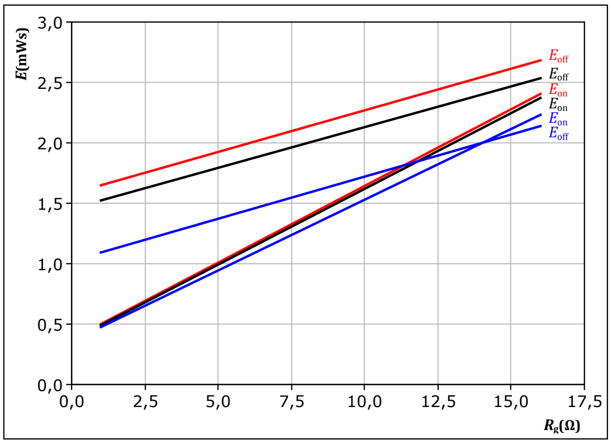
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	4	Ω		150 °C
R_{goff} =	4	Ω		

figure 25. **IGBT**

Typical switching energy losses as a function of IGBT turn on gate resistor

$E = f(R_g)$



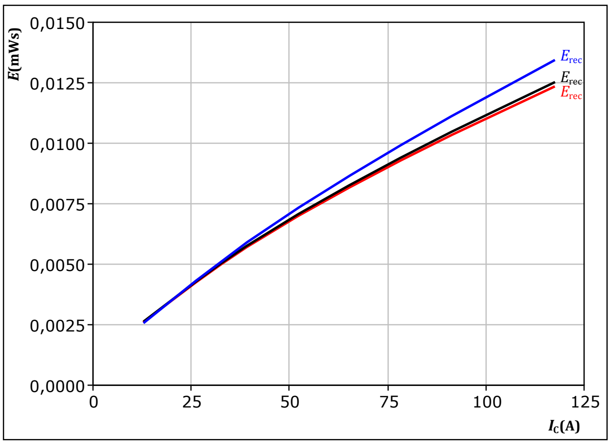
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	65	A		150 °C

figure 26. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_C)$



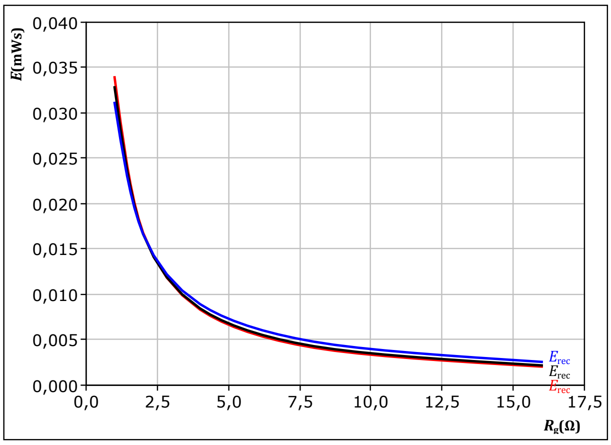
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	4	Ω		150 °C

figure 27. **FWD**

Typical reverse recovered energy loss as a function of IGBT turn on gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

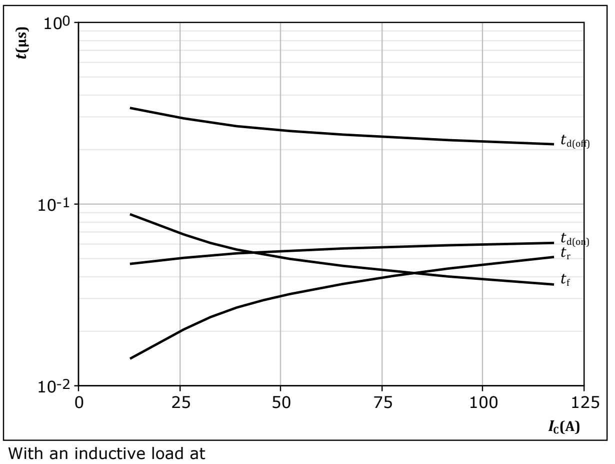
V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	65	A		150 °C

Negative Neutral Point Switching Characteristics

figure 28. **IGBT**

Typical switching times as a function of collector current

$t = f(I_C)$



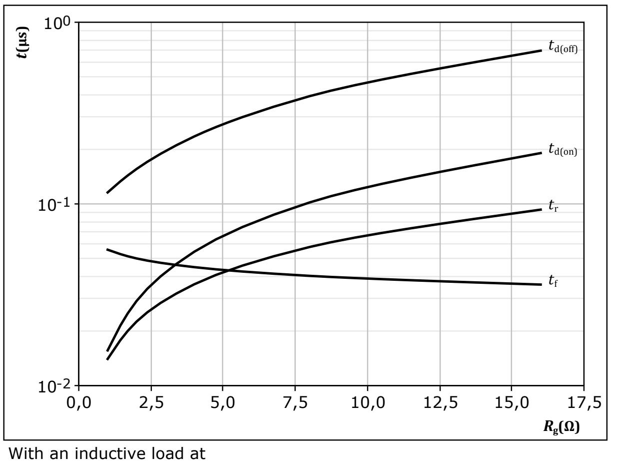
With an inductive load at

T_j =	150	°C
V_{CE} =	400	V
V_{GE} =	0/15	V
R_{gon} =	4	Ω
R_{goff} =	4	Ω

figure 29. **IGBT**

Typical switching times as a function of IGBT turn on gate resistor

$t = f(R_g)$



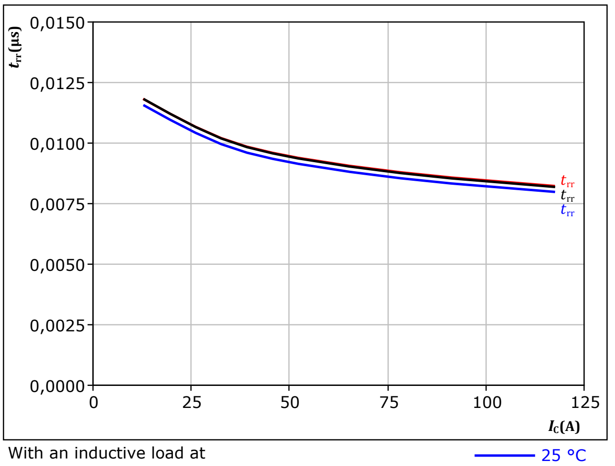
With an inductive load at

T_j =	150	°C
V_{CE} =	400	V
V_{GE} =	0/15	V
I_C =	65	A

figure 30. **FWD**

Typical reverse recovery time as a function of collector current

$t_{rr} = f(I_C)$



With an inductive load at

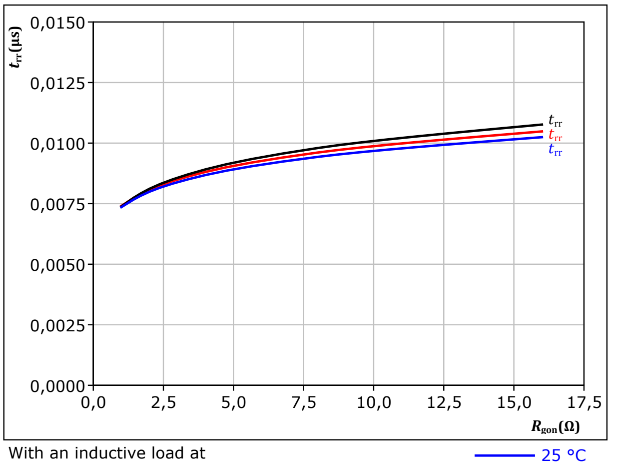
V_{CE} =	400	V
V_{GE} =	0/15	V
R_{gon} =	4	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 31. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

$t_{rr} = f(R_{gon})$



With an inductive load at

V_{CE} =	400	V
V_{GE} =	0/15	V
I_C =	65	A

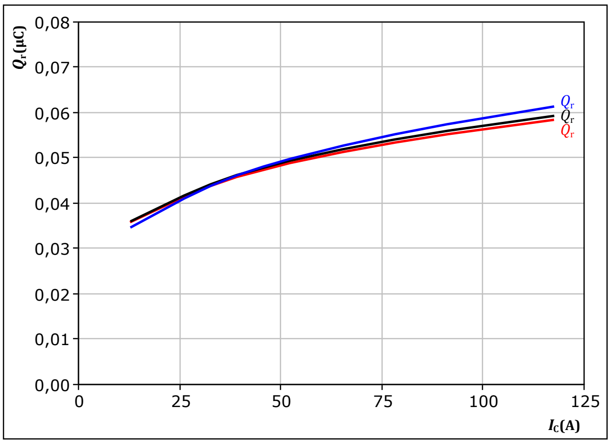
T_j: 25 °C, 125 °C, 150 °C

Negative Neutral Point Switching Characteristics

figure 32. **FWD**

Typical recovered charge as a function of collector current

Q_r = f(I_C)



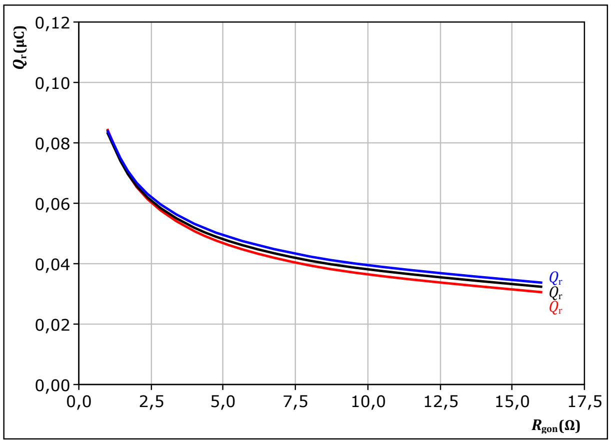
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	4	Ω		150 °C

figure 33. **FWD**

Typical recovered charge as a function of IGBT turn on gate resistor

Q_r = f(R_{gon})



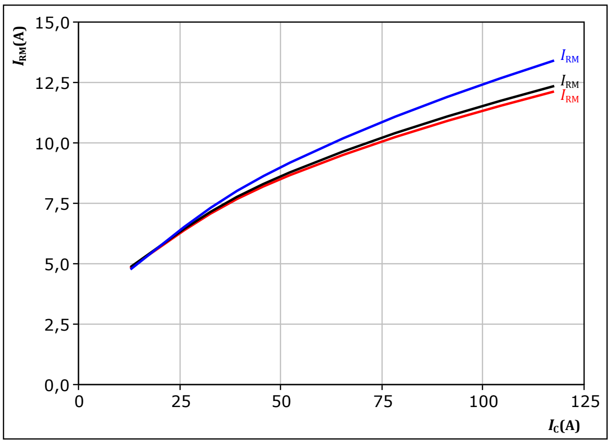
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	65	A		150 °C

figure 34. **FWD**

Typical peak reverse recovery current as a function of collector current

I_{RM} = f(I_C)



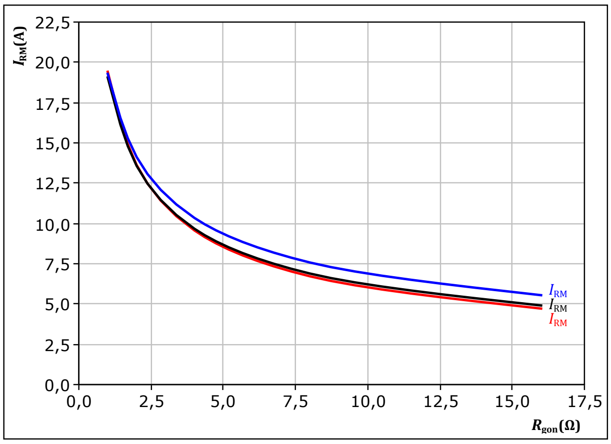
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	4	Ω		150 °C

figure 35. **FWD**

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

I_{RM} = f(R_{gon})



With an inductive load at

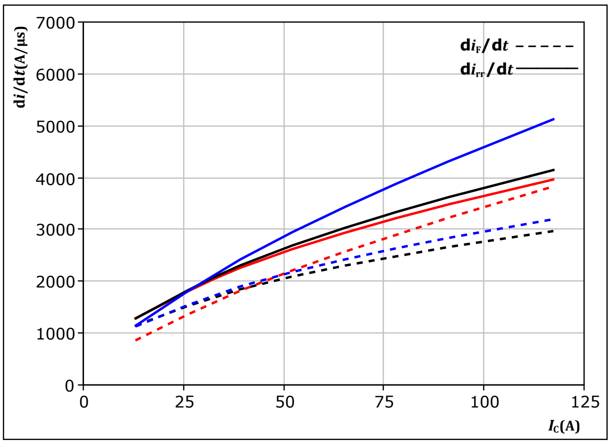
V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	65	A		150 °C

Negative Neutral Point Switching Characteristics

figure 36. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

di_F/dt, di_{rr}/dt = f(I_C)



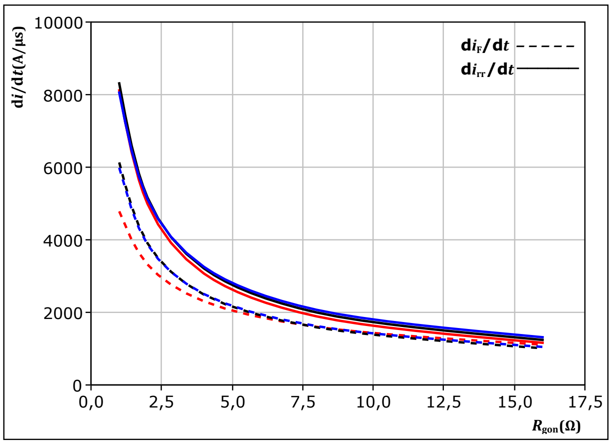
With an inductive load at

V_{CE} =	400	V	T_j: 25 °C
V_{GE} =	0/15	V	125 °C
R_{gon} =	4	Ω	150 °C

figure 37. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})



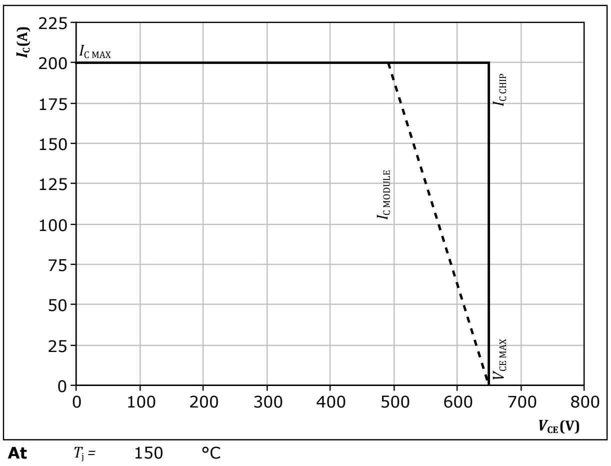
With an inductive load at

V_{CE} =	400	V	T_j: 25 °C
V_{GE} =	0/15	V	125 °C
I_C =	65	A	150 °C

figure 38. **IGBT**

Reverse bias safe operating area

I_C = f(V_{CE})



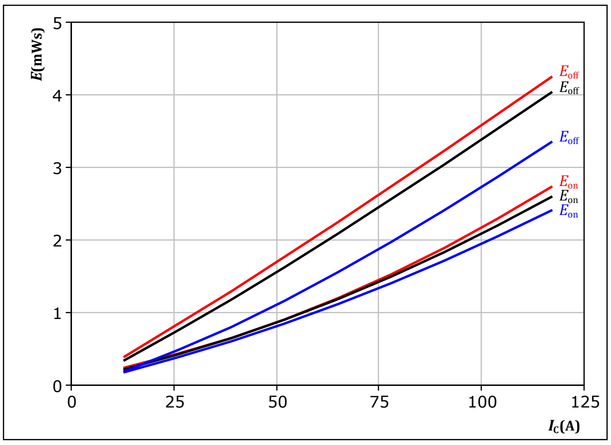
At	T_j =	150	°C
	R_{gon} =	4	Ω
	R_{goff} =	4	Ω

Positive Neutral Point Switching Characteristics

figure 39. **IGBT**

Typical switching energy losses as a function of collector current

E = f(I_C)



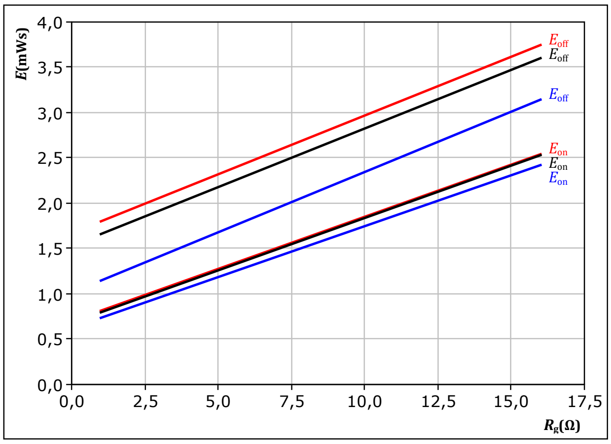
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	4	Ω		150 °C
R_{goff} =	4	Ω		

figure 40. **IGBT**

Typical switching energy losses as a function of IGBT turn on gate resistor

E = f(R_g)



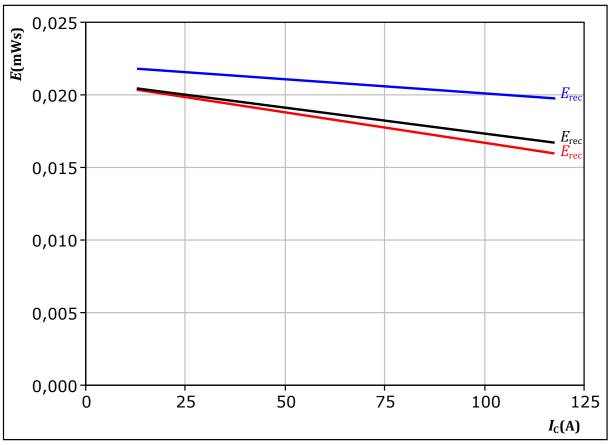
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	65	A		150 °C

figure 41. **FWD**

Typical reverse recovered energy loss as a function of collector current

E_{rec} = f(I_C)



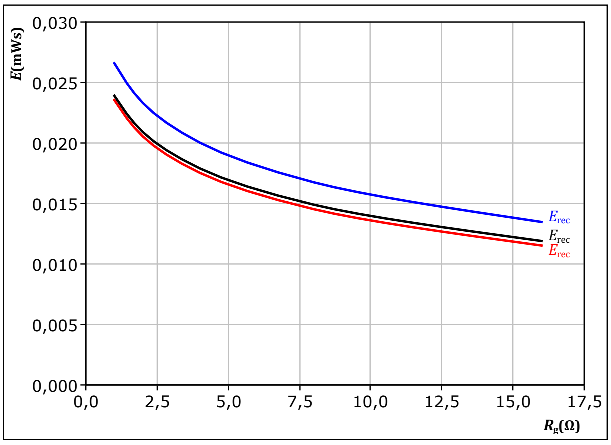
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	4	Ω		150 °C

figure 42. **FWD**

Typical reverse recovered energy loss as a function of IGBT turn on gate resistor

E_{rec} = f(R_g)



With an inductive load at

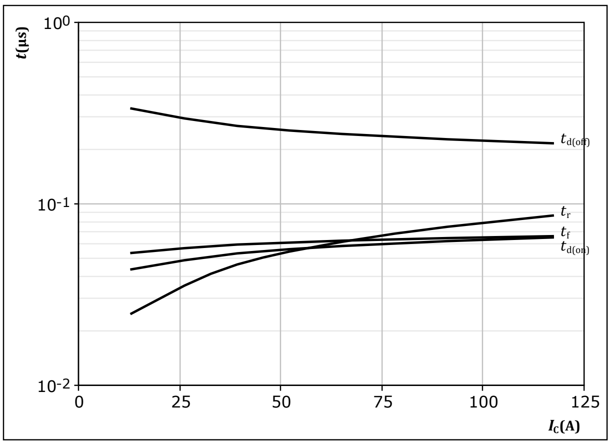
V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	65	A		150 °C

Positive Neutral Point Switching Characteristics

figure 43. **IGBT**

Typical switching times as a function of collector current

t = f(I_C)



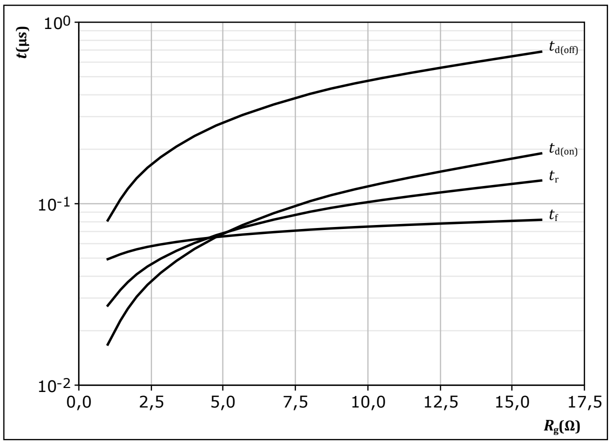
With an inductive load at

T_j =	150	°C
V_{CE} =	400	V
V_{GE} =	0/15	V
R_{gon} =	4	Ω
R_{goff} =	4	Ω

figure 44. **IGBT**

Typical switching times as a function of IGBT turn on gate resistor

t = f(R_g)



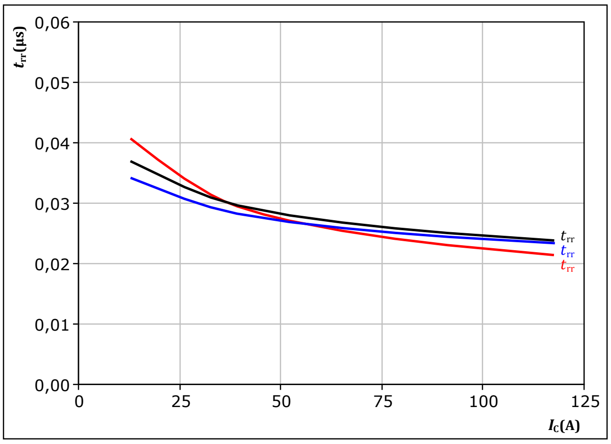
With an inductive load at

T_j =	150	°C
V_{CE} =	400	V
V_{GE} =	0/15	V
I_C =	65	A

figure 45. **FWD**

Typical reverse recovery time as a function of collector current

t_{rr} = f(I_C)



With an inductive load at

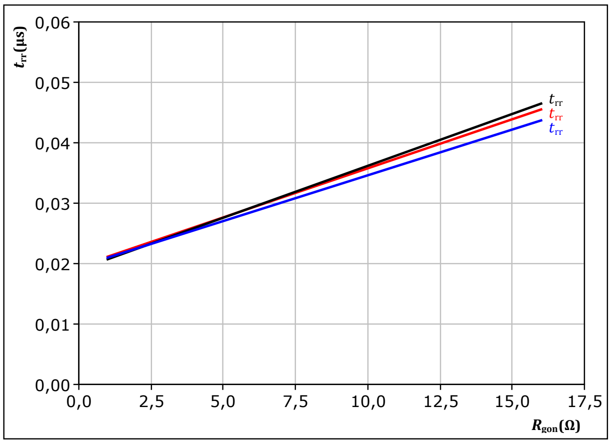
V_{CE} =	400	V
V_{GE} =	0/15	V
R_{gon} =	4	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 46. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

t_{rr} = f(R_{gon})



With an inductive load at

V_{CE} =	400	V
V_{GE} =	0/15	V
I_C =	65	A

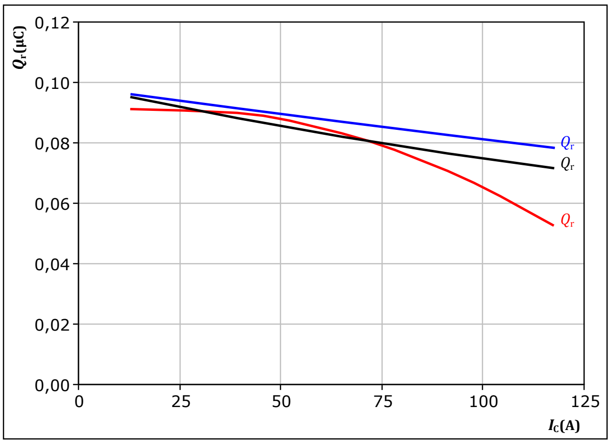
T_j: 25 °C, 125 °C, 150 °C

Positive Neutral Point Switching Characteristics

figure 47. **FWD**

Typical recovered charge as a function of collector current

Q_r = f(I_C)



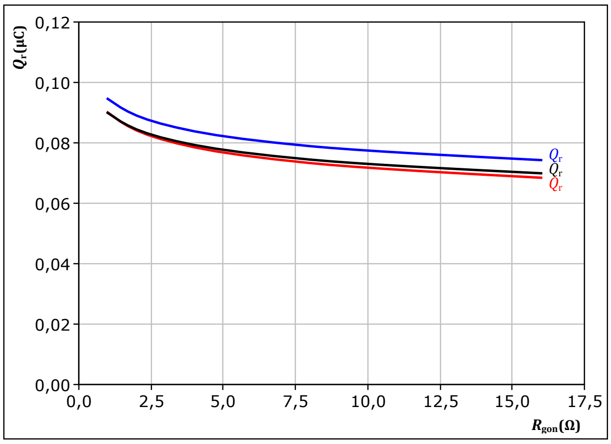
With an inductive load at

V_{CE} =	400	V	T_j: 25 °C / 125 °C / 150 °C
V_{GE} =	0/15	V	
R_{gon} =	4	Ω	

figure 48. **FWD**

Typical recovered charge as a function of IGBT turn on gate resistor

Q_r = f(R_{gon})



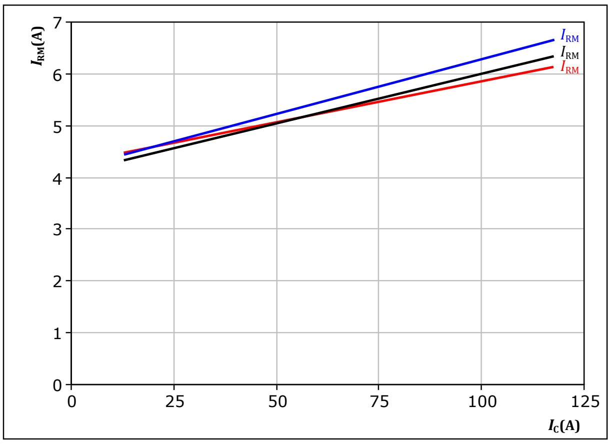
With an inductive load at

V_{CE} =	400	V	T_j: 25 °C / 125 °C / 150 °C
V_{GE} =	0/15	V	
I_C =	65	A	

figure 49. **FWD**

Typical peak reverse recovery current as a function of collector current

I_{RM} = f(I_C)



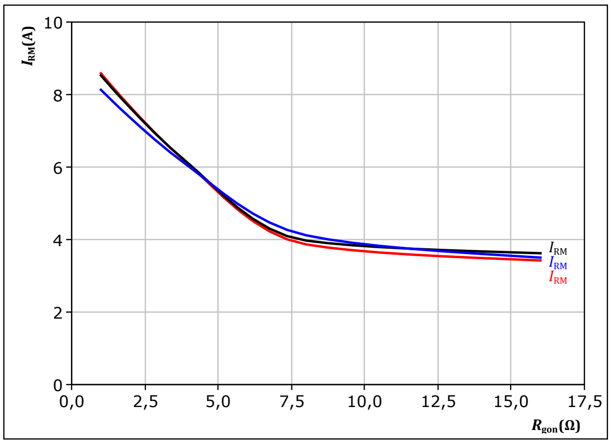
With an inductive load at

V_{CE} =	400	V	T_j: 25 °C / 125 °C / 150 °C
V_{GE} =	0/15	V	
R_{gon} =	4	Ω	

figure 50. **FWD**

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

I_{RM} = f(R_{gon})



With an inductive load at

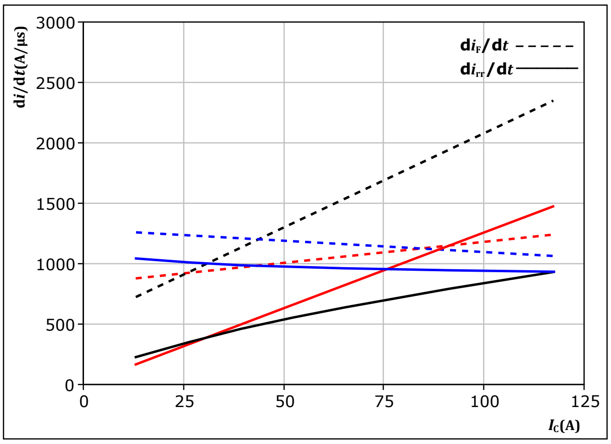
V_{CE} =	400	V	T_j: 25 °C / 125 °C / 150 °C
V_{GE} =	0/15	V	
I_C =	65	A	

Positive Neutral Point Switching Characteristics

figure 51. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

di_F/dt, di_{rr}/dt = f(I_C)



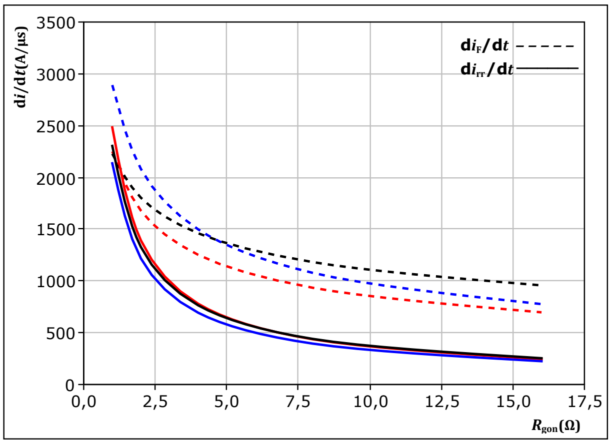
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	4	Ω		150 °C

figure 52. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})



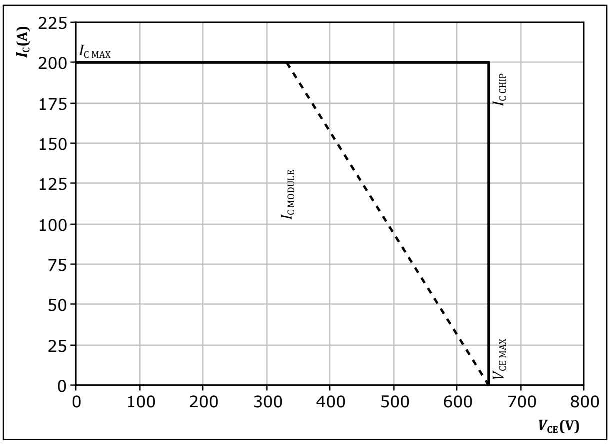
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	65	A		150 °C

figure 53. **IGBT**

Reverse bias safe operating area

I_C = f(V_{CE})



At	T_j =	150	°C
	R_{gon} =	4	Ω
	R_{goff} =	4	Ω

Switching Definitions

figure 54. **IGBT**

Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{tEoff} = integrating time for E_{off})

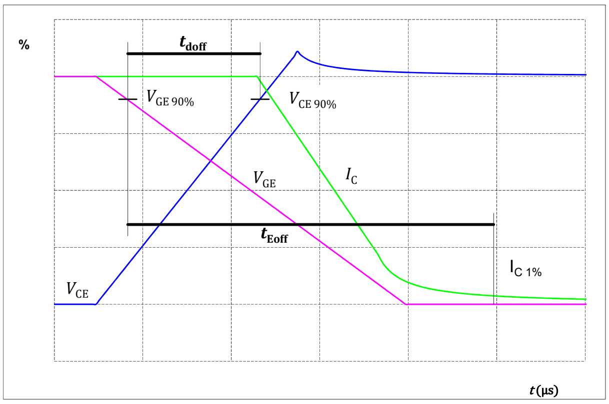


figure 55. **IGBT**

Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} = integrating time for E_{on})

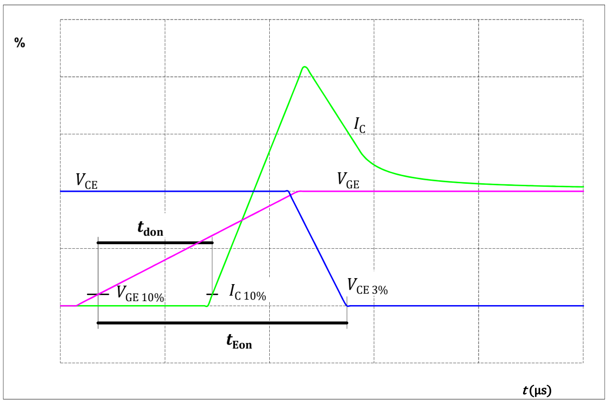


figure 56. **IGBT**

Turn-off Switching Waveforms & definition of t_f

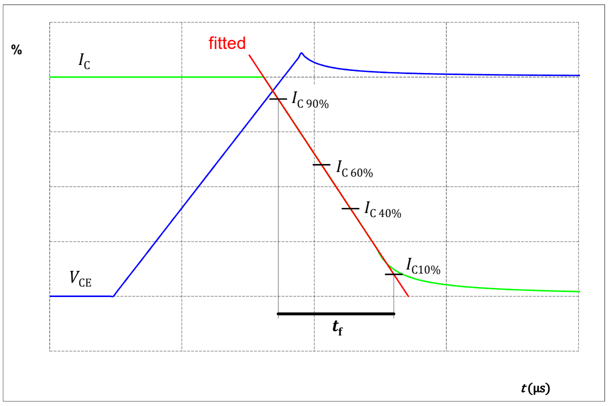
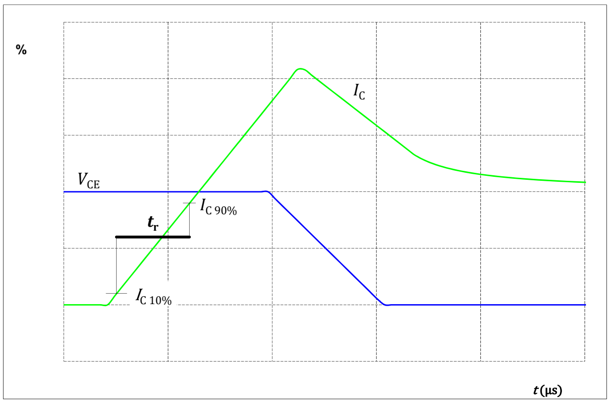


figure 57. **IGBT**

Turn-on Switching Waveforms & definition of t_r



Switching Definitions

figure 58. **FWD**

Turn-off Switching Waveforms & definition of t_{rr}

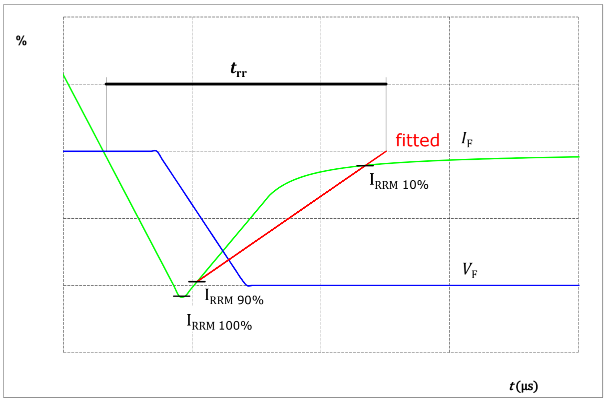
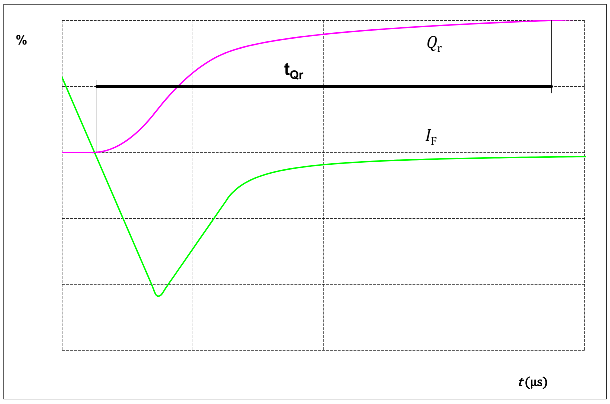


figure 59. **FWD**

Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)



Ordering Code

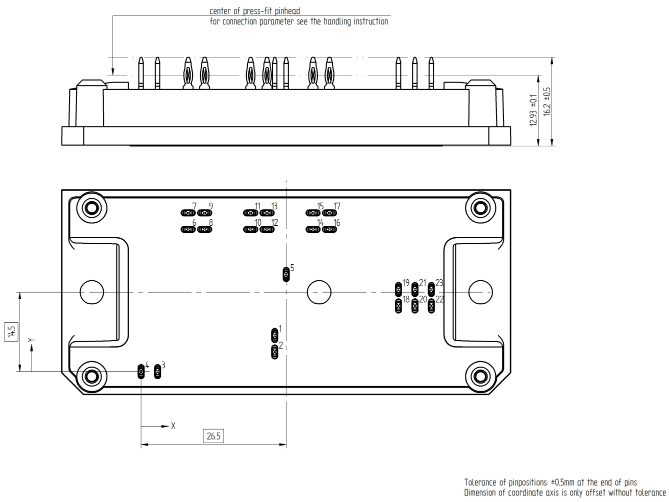
Version	Ordering Code
Without thermal paste	10-PY07ANA100RG01-LH23L68Y
With thermal paste (5,2 W/mK, PTM6000HV)	10-PY07ANA100RG01-LH23L68Y-/7/
With thermal paste (3,4 W/mK, PSX-P7)	10-PY07ANA100RG01-LH23L68Y-/3/

Marking

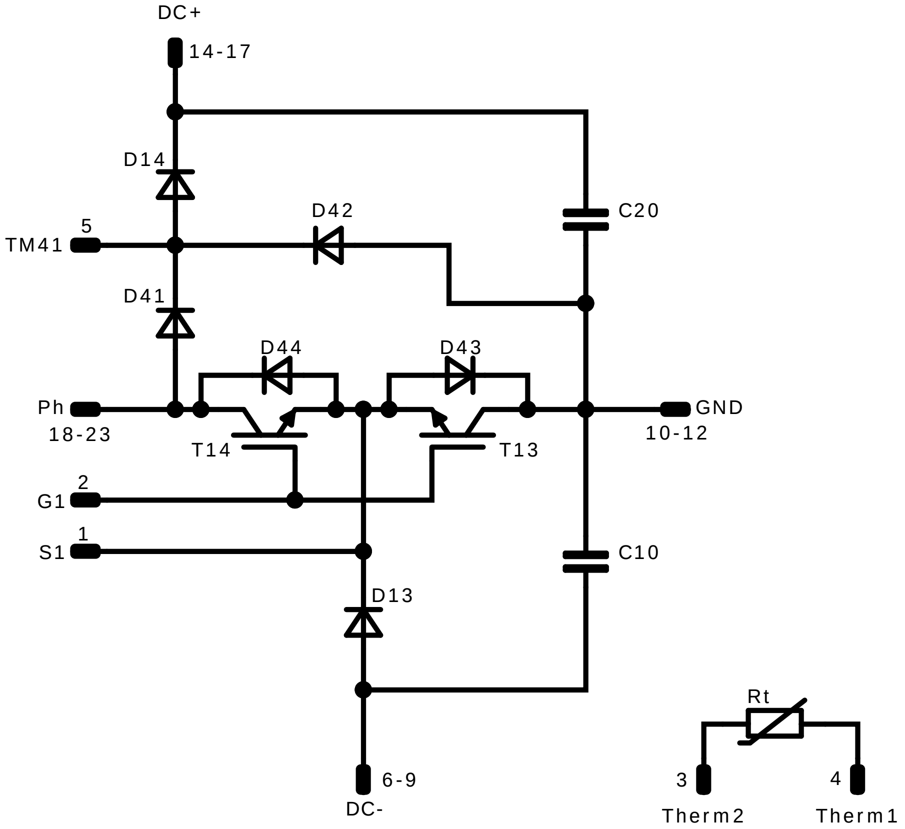
	Name		Date code	UL & VIN	Lot	Serial
Text	NN-NNNNNNNNNNNNNN-TTTTTTVV		WWYY	UL VIN	LLLLL	SSSS
	Type&Ver	**Lot number**	**Serial**	**Date code**		
Datamatrix	TTTTTTTVV	LLLLL	SSSS	WWYY		

Outline

Pin	X	Y	Function
Pin table [mm]			
1	24,4	6,6	S1
2	24,4	3,6	G1
3	3	0	Therm2
4	0	0	Therm1
5	26,5	17,75	TM41
6	8,6	26	DC-
7	8,6	29	DC-
8	11,6	26	DC-
9	11,6	29	DC-
10	20	26	GND
11	20	29	GND
12	23	26	GND
13	23	29	GND
14	31,4	26	DC+
15	31,4	29	DC+
16	34,4	26	DC+
17	34,4	29	DC+
18	47	12	Ph
19	47	15	Ph
20	50	12	Ph
21	50	15	Ph
22	53	12	Ph
23	53	15	Ph



Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T13	IGBT	650 V	100 A	Negative Neutral Point Switch	
T14	IGBT	650 V	100 A	Positive Neutral Point Switch	
D13	FWD	650 V	30 A	Negative Boost Diode	
D14	FWD	650 V	30 A	Positive Boost Diode	
D43	Rectifier	1600 V	60 A	Negative Neutral Point Diode	
D44	Rectifier	1600 V	110 A	Positive Neutral Point Diode	
D42	FWD	650 V	20 A	Positive Boost Diode Protection Diode	
D41	Rectifier	1600 V	60 A	Positive Boost Blocking Diode	
C10, C20	Capacitor	630 V		Capacitor (DC)	
Rt	Thermistor			Thermistor	

Packaging instruction				
Standard packaging quantity (SPQ) 100	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* 1 packages see vincotech.com website.

Package data
Package data for *flow* 1 packages see vincotech.com website.

Vincotech thermistor reference
See Vincotech thermistor reference table at vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
10-PY07ANA100RG01-LH23L68Y-D1-14	19 Apr. 2022		